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wherein said element is generally laterally coextensive with said intervening insulating region.

61. The method in claim 60, wherein said step of depositing a generally insulative material comprises depositing a generally insulative material that is allowed to comprise oxide charges.

62. The method in claim 61, further comprising a step of plasma treating said substrate prior to said step of depositing an oxide charge barrier.

63. The method in claim 61, further comprising:

annealing said generally insulative material;

allowing an oxide charge in said generally insulative material to migrate toward said substrate in response to said annealing step; and

intercepting said oxide charge with said oxide charge barrier before said oxide charge reaches said substrate.

64. The method in claim 61, further comprising refraining from depositing any generally conductive material before said step of depositing a generally insulative material.

Please cancel claims 36-51 without prejudice.

REMARKS

Claims 52-64 are the only claims pending as of this Preliminary Amendment. Per a telephone conversation held with the Examiner of the parent application on July 19, 1999, Applicants elected to pursue the device claims (claims 36-51) during prosecution of that application. Accordingly, Applicants seek to pursue the method claims (52-64) in this divisional application. If there are any matters which may be resolved or clarified through a telephone interview, the Examiner is requested to contact Applicants' undersigned attorney at the number indicated.

Respectfully submitted,

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